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DEFECT CONTROL IN SEMICONDUCTORS

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the Science and Technology of Defect Control in Semiconductors
The Yokohama 21st Century Forum
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PREFACE

This book contains 254 papers presented at "The International Conference on the Science and Technology of Defect Control in Semiconductors (IC-STDSCS)" which was held on September 17-22, 1989 in Yokohama, Japan. The conference was organized as *The Yokohama 21st Century Forum 1989* to commemorate the centenary of Yokohama City.

Defect control in semiconductors is a key technology for realizing the ultimate possibilities of modern electronics. It is obvious that the basis for such control lies in an integrated knowledge of a variety of defect properties. From this viewpoint, the aim of the conference was to provide a forum for the discussion of defect-related problems in connection with defect control in semiconducting materials. The organizers of the conference especially hoped that scientists in the field of basic research and engineers involved in application related to electronic devices could mutually benefit from joint discussion.

Basic research on defects in semiconductors seems to have initially started with the question of what effects appear if the regular tetrahedral coordination of a typical semiconductor is disturbed locally by the introduction of some structural defects or impurities which have different valences, different sizes and different inner shells. A large number of papers have so far been published in this research field. The problems have also been discussed at a series of international conferences such as the ICDS. Fairly great progress seems to have been achieved in this field, especially in understanding the nature of relatively simple types of defects. However, the field of research is now expanding very rapidly, and defects to be investigated are becoming more and more complicated.

On the one side, the study of defects in semiconductors is becoming increasingly important to the field of applications as great progress is made in electronic device technology on the basis of developments in material-processing of semiconductors. In the early stages of the study, only negative or harmful aspects of defects were recognized. Thus, defect study in this field initially focused on finding methods of suppressing or avoiding generation of harmful defects during crystal growth or device processing in order to facilitate device fabrication. Recently, a new trend has appeared in which defects are positively utilized to improve device performance and reliability. Typical examples are intrinsic and extrinsic gettering techniques in silicon technology and utilization of EL2 to achieve semi-insulation of GaAs. The most important matter now seems to be to find ways to control the distribution, density and even properties of any defects rather than to completely eliminate such defects from crystals.

As a matter of fact, when materials engineers of electronic devices attempt to apply the results of basic research, they often feel that these results are too basic to yield practical and profitable results in device fabrication. As a consequence, a considerable share of the development in the modern technology of electronic materials now seems to result from experiences practically encountered during device fabrication processes. Various technological difficulties have been practically overcome by means of such trial and error. Conversely, when scientists involved in basic research observe any defect-related phenomena which are encountered in device fabrication processes, they recognize that the phenomena are usually too complicated to allow for any immediate self-consistent interpretation. Most of the important processes take place at high temperatures where various types of reactions can occur among numerous kinds of defects and impurities by means of thermal activation.

However, it is obvious that no matter how complicated the phenomena seem to be, they are just the results of accumulation of elementary processes which are rate-controlled by the behaviour of simple types of defects and impurities. Even when engineers practically develop a new technology on the basis of their experience in device production processes, it can be achieved more efficiently if they understand the underlying physical phenomena correctly. So, engineers need to deepen their knowledge of the basic properties of defects. At the same time, it seems true that various phenomena encountered in the practical field often lead scientists to new fields of research. Phenomena really occurring in nature are much richer in variety than those human brains can imagine. Actually many basic studies of semiconductor defects now being done have their origin in practical device production processes.

At any rate, the organizers of the conference believed that exchange between scientists and engineers in the field of semiconductor defects was becoming more and more important, and this idea motivated them to organize this conference. Indeed, human history after the Industrial Revolution tells us that progress in natural science and development of technology are mutually dependent and inseparable. This proposition is obvious also in the rather narrow field of semiconductor defects.

Over 460 participants from 24 different countries attended the conference. Discussion at each technical session was extremely active. The organizers of the conference were well satisfied that their intention in organizing the conference had been understood by all participants.

The papers submitted to the conference have all been reviewed and revised as required in preparation for publication. They have been organized into seven sections in this book, namely, General, Silicon, Bulk Compounds, Thin Layers and Heterostructure, Dislocations and Deformation-induced Defects, Defect Characterization, and Organic Crystals. Although the editor realizes that this is by no means a unique way of classifying the papers, he feels that this classification to some extent reflects the present level of the science and technology of semiconductor materials. He feels also that the conference itself was a significant experiment for finding the most effective way of bringing together scientists involved in basic research and engineers seeking to apply such research.

K. Sumino

Acknowledgement

Many colleagues from both universities and industries of Japan participated eagerly in organizing the conference. Especially, Dr. S. Kawado, Dr. J. Matsui, Dr. N. Inoue and Professor K. Kojima served as session-chairpersons and were in charge of organizing sessions related to Silicon, Bulk Compounds, Thin Layers and Heterostructure, and Organic Crystals, respectively. Dr. I. Yonenaga and Mrs. U. Onose served as conference secretaries. We thank all of the colleagues for their efforts which made the conference successful. We are also grateful to many Japanese industries for their financial support of the conference.

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CONTENTS

VOLUME I

PART I. GENERAL

Defect engineering in semiconductors through defect control: An historical perspective[†]	
H.C. Gatos	3
Fundamental limits in semiconductor materials processing[†]	
L.C. Kimerling	17
The importance of interaction between theory and experiment in understanding and identifying technologically important point defects[†]	
G.A. Baraff	31
Resolving defect mega-controversy by giga-event Monte Carlo simulation of the macro-consequences of atom-level assumptions on microcomputers at Nano-cost[†]	
J.A. Van Vechten, U. Schmid and N.C. Myers	41
Hydrogen in semiconductors[†]	
J.W. Corbett, S.J. Pearton and M. Stavola	53
Light impurities in semiconductors[†]	
R.C. Newman	65
Non-equilibrium point defects and diffusion in silicon and gallium arsenide[†]	
U. Gösele, B.P.R. Marioton and T.Y. Tan	77
Gettering of transition metals in semiconductors[†]	
E.R. Weber and D. Gilles	89
The mechanisms of electronically enhanced defect reactions in semiconductors[†]	
M.K. Sheinkman and L.C. Kimerling	97
Control of radiation resistance in solar cells[†]	
A.F.W. Willoughby	107
Atomic-scale characterization and control of interface roughness and corrugation in quantum heterostructures[†]	
H. Sakaki, M. Tanaka, T. Noda and J. Motohisa	119
Surface processes on Si and GaAs studied by in-situ electron microscopy[†]	
N. Inoue	129

[†] Invited paper.

PART II. SILICON

Section II.1: Grown-in defects

Origin and effects of inhomogeneous impurity distribution in CZ silicon [†]	
W. Zulehner	143
Ring-likely distributed stacking faults in CZ-Si wafers	
M. Hasebe, Y. Takeoka, S. Shinoyama and S. Naito	157
The inhomogeneity of oxygen precipitate in Czochralski-grown silicon crystal	
M. Imai and Y. Yatsurugi	163
Positron annihilation parameter and defects in monocrystalline silicon	
K. Kitagawa, K. Yamashita, H. Murakami, I. Kanazawa and T. Shiraiwa	169
Synchrotron X-ray diffraction topography of growth striation and microdefects in MCZ silicon single crystals	
S. Kawado, S. Kojima, Y. Kato, H. Hayashi and T. Ishikawa	175
Effects of magnetic field on the perfection of MCZ silicon	
Z. Mai, Z. Mao, S. Cui, C. Wang, L. Wu, H. Li, G. Chen, S. Zhou and S. Ye	181
Observation of D-defects and growth striations in FZ-silicon crystals by synchrotron radiation section topography	
Y. Sugita, S. Iida, H. Takeno, Y. Yagou, N. Kasagi, H. Kawata, J. Chikawa and T. Abe	187

Section II.2: Oxygen-related defects

Diffusion and aggregation of oxygen impurities in silicon	
A. Oshiyama and M. Saito	193
Effects of various pre-treatments and impurity content on thermal donor formation in silicon [†]	
L.I. Murin and V.P. Markevich	199
Hydrogen-assisted thermal donor formation in silicon [†]	
H.J. Stein and S. Hahn	211
Formation of thermal and new donors in CZ-silicon wafers	
S. Nouredin and T. Kormány	221
Thermal donor formation in oxygen-implanted float zone silicon	
S. Hahn, H.J. Stein, S.C. Shatas and F.A. Ponce	227
Oxygen precipitation at 400–700°C in Czochralski silicon: Thermal donors, new donors and rod-like defects	
Y. Kamiura, F. Hashimoto and M. Yoneta	233
New aspects of modelling the oxygen precipitation in CZ-silicon	
M. Reiche	239

[†] Invited paper.

Computer aided investigation of oxygen precipitation M. Schrems, T. Brabec, M. Budil, H. Pötzl, E. Guerrero, D. Huber and P. Pongratz	245
The stability of platelike oxide precipitates in CZ-silicon J. Jablonski	251
Role of oxygen in nucleation of microprecipitates in silicon materials P. Gall, J.-P. Fillard, J. Bonnafé, T. Rakotomavo, H. Rüfer and H. Schwenk	255
Diffuse X-ray scattering of thermally annealed p-type Czochralski silicon D.A.P. Bulla, W.E. Castro Jr., V. Stojanoff and S. Hahn	261
Study of oxide precipitates in MCZ-silicon crystals by the Pendellösung fringe method Y. Sugita, S. Iida, H. Takeno, N. Kasagi and H. Kawata	267
Generation of silicon interstitials by thermal oxidation of silicon wafers M. Umeno, S. Baba, T. Kojima and N. Ohmae	273
<i>Section II.3: Metallic impurities and gettering</i>	
Complex formation of transition element impurities in silicon [†] C.A.J. Ammerlaan and A.B. Van Oosten	279
Energy levels related to substitutional gold in silicon M. Morooka, H. Tomokage and M. Yoshida	291
The contrastive behavior of Fe and Cu impurities in Si crystals [†] T. Abe, T. Itoh, Y. Hayamizu, K. Sunagawa, S. Yokota and H. Yamagishi	297
The behavior of defects induced by Fe, Ni, and Cu contamination on Si surfaces M. Hourai, S. Sadamitsu, K. Murakami, T. Shigematsu and N. Fujino	305
/ Characterization of cleanliness of annealing furnace by lifetime measurements Y. Takano	311
Permeation of copper into silicon at room temperature P. Jones, Y. Zhang, J. Liu, J.-Z. Yuan, C. Ortiz, B. Baufeld, H. Bakhru, J.W. Corbett and S.J. Pearton	317
Electrical degradation of silicon due to mercury contamination P. Jones and J.W. Corbett	321
Internal gettering of iron in Czochralski-silicon: Model and quantitative analysis D. Gilles, E.R. Weber, S. Hahn and K. Cho	323
Iron gettering by high energy ion implantation Y. Niki, S. Nadahara and M. Watanabe	329

[†] Invited paper.

Section II.4: Defect reactions and passivation

Generation and annihilation of iron–boron pairs in silicon M. Suezawa and K. Sumino	335
Carbon-related defects in silicon P.J. Drevinsky, C.E. Cafer, L.C. Kimerling and J.L. Benton	341
Microscopic nature of lithium interaction with acceptor-type defects in silicon G.S. Myaken'kaya, G.L. Gutsev, N.P. Afanasyeva, V.A. Evseev and R.F. Konopleva	347
Point defect generation and arsenic diffusion in silicon in inert ambient A. Bakowski	353
Thermally induced acceptor levels and their annealing behavior in n-type silicon M. Yoneta, Y. Kamiura and F. Hashimoto	359
Study of quenched-in defects in silicon by EBIC method T. Iwasaki, T. Sekiguchi, Y. Miyamura and K. Sumino	365
Quenched-in defects in silicon U. Reislohner, S. Deubler, P. Dohlus, D. Forkel, J. Meier, H. Wolf, W. Witthuhn and H. Prigge	371
Identification of process-induced defects in silicon by PAC R. Keller, M. Deicher, W. Pfeiffer, H. Skudlik, D. Steiner and Th. Wichert	377
Isovalent impurities in silicon: Elastic stresses, thermodonors, defect–impurity interaction L.I. Khirunenko, V.E. Kustov and V.I. Shakhovtsov	383
On the impurity gettering in neutron transmutation doped Si (Ge) A.V. Voevodova, F.P. Korshunov, N.A. Sobolev and A.A. Stuk	387
Calculation of interaction energy between impurities and lattice defects in semiconductor crystals: Interpretation of impurity gettering K. Masuda-Jindo	393
Defect formation and impurity redistribution near interfaces in silicon V.V. Bolotov, M.D. Efremov, V.M. Emeksuzyan, V.A. Stuchinsky and K. Schmalz	399
Grain boundaries-metallic impurities interactions investigated by scanning MCTS T. Heiser, A. Mesli and P. Siffert	407
Stability of acceptor-hydrogen complexes in semiconductors H. Skudlik, M. Deicher, R. Keller, W. Pfeiffer, D. Steiner and Th. Wichert	413
Quenching of hydrogenated silicon: H-related defects generation A. Mesli, T. Heiser and P. Siffert	419
Optical properties of hydrogen-related shallow donor in c-Si:H S. Tokmoldin, B. Mukashev, M. Tamendarov and S. Chasnikova	425

Vibrational spectra of hydrogen-related centres in silicon B. Mukashev, S. Tokmoldin and M. Tamendarov	429
Neutralization of electrically active defects in silicon G.S. Myaken'kaya, G.L. Gutsev and N.N. Gerasimenko	435
Isolated impurity for substituting elements of 2D and 3D periods in a neutral charge state in crystal silicon G.S. Myakenkaya, G.L. Gutsev and N.N. Gerasimenko	441
Motional effects and optical pumping effects of off-center substitutional nitrogen in silicon K. Murakami, H. Kuribayashi, K. Hara and K. Masuda	447
<i>Section II.5: Defects induced by ion-implantation or dry etching</i>	
Interactions between oxygen atoms and defects induced by high-energy ion implantation† M. Tamura	453
Formation of high concentration oxygen layer in high energy ion implanted Si S. Nadahara, Y. Niki and M. Watanabe	465
On the electronic structure of implanted semiconductors E. Antoncik	471
Damage formed by ion implantation in silicon evaluated by Rutherford backscattering, reflected high energy electron diffraction and thermal wave modulated optical reflectance T. Hara, S. Takahashi, H. Hagiwara, W.L. Smith, C. Welles, S. Hahn, L. Larson and C.C.D. Wong	477
Investigations of the amorphous/crystalline phase transition in ion-implanted silicon layers by means of cross-sectional TEM H. Bartsch	483
An anomalous redistribution of B in doubly As and B implanted silicon during annealing K. Yokota, M. Ochi and T. Hirao	489
Depth profiles of vacancy-type defects in ion-implanted Si studied by monoenergetic positron beam A. Uedono, S. Tanigawa, J. Sugiura and M. Ogasawara	495
Damage studies in hydrogen implanted (001) silicon J. Vanhellefont, C. Claeys and H.E. Maes	501
Microstructure of radiation damage in silicon after reactive ion etching H. Cerva and H.P. Strunk	507
Optical characterization of defects created in semiconductors by plasma etching processes J. Weber and W.D. Sawyer	513
Defect formation and gettering effect in plasma etched silicon S.V. Koveshnikov, E.B. Yakimov, N.A. Yarykin and V.A. Yunkin	519

† Invited paper.

Section II.6: Irradiation-induced defects

Self-organization and instability in the system of defects in semiconductors under irradiation J.W. Corbett, N.N. Gerasimenko and I.V. Verner	525
Localized states in crystalline electron irradiated semiconductors S.D. Kouimtzi	529
Effect of thermal pretreatment on nucleation of electron irradiation induced secondary defects in silicon G.-C. Hua, R. Oshima and F.E. Fujita	535
Enhanced annealing of radiation defects in pre-heat-treated Si crystals F.P. Korshunov, L.F. Makarenko, V.P. Markevich, I.F. Medvedeva and L.I. Murin	541
Effects of oxygen donors and irradiating energy on radiation defects in silicon N. Fukuoka, K. Nakata, M. Honda, K. Atobe and T. Kawakubo	547
Defect formation and lifetime control by electron irradiation in a special NTD silicon F.-m. Wu, Y. Shi, C.-h. Wang, F.-l. Zhou and Y.-s. Wang	553
Defect control in irradiated silicon by near edge luminescence spectroscopy F.P. Korshunov, N.A. Sobolev and V.A. Sheraukhov	559

Section II.7: Defect control and device performance

Advances in engineering and control of process-induced defects in silicon [†] C. Claeys and J. Vanhellemont	565
Defect engineering for ULSI epitaxial silicon [†] G.A. Rozgonyi and R.R. Kola	579
Nondestructive, real-time monitoring of heavy metal contamination and efficiency of internal gettering during IC processing by surface photovoltage technique – A review [†] L. Jastrzebski	593
Interrelation between starting parameters and process-induced properties of CZ-silicon wafers [†] H. Richter, F.-G. Kirscht, P. Fricke, T. Flade and J. Reichel	605
PIN/MOSFET fabrication using laser induced defects in silicon T. Mada, N. Inoue, M. Kawachi and M. Yasu	615
Crystalline defect generation and suppression in submicron VLSI N. Tsuchiya and Y. Matsushita	621
Effects of various intrinsic gettering treatments upon thin gate oxide integrity in high carbon content CZ Si S. Hahn, C.Y. Tung, J. Lee, J. Partanen and T. Tuomi	627

[†] Invited paper.

Effects of Czochralski Si substrate material parameters upon 16 ns 256k SRAM yield and device performance	
K. Choi, S. Hahn, K. Cho, J. Partanen and T. Tuomi	633
Defects in MOS technologies	
D. Korytár, P. Kavický, M. Hulman, A. Weissensteiner, Ľ. Tuchscher and P. Gerát	639
Degradation of h_{FE} resulting from lattice defects in the collector region	
H. Ohyama and K. Nemoto	645

PART III. BULK COMPOUNDS

Section III.1: Grown-in defects in III-V compounds

The growth of high quality III-V crystals by the vertical gradient freeze method [†]	
W.A. Gault, J.E. Clemans, J.H. Conway, F. Dominquez, T.I. Ejim, E.M. Monberg and F. Simchock	653
Dislocations and electric characteristics of ion-implanted layers in liquid-encapsulated, vertical-Bridgman GaAs crystals	
K. Ikuta, H. Nakanishi, H. Kohda and K. Hoshikawa	661
Solid-liquid interface shape and characteristic structural defects in gallium arsenide single crystals grown by the gradient freeze method	
K. Fujii, M. Hirata, H. Fujita and S. Takeda	667
X-ray topographic study of lattice strain in a cellular structure of undoped LEC GaAs crystal	
T. Kitano, T. Ishikawa and J. Matsui	673
Generation of dislocations and their interaction with point defects in LEC GaAs: Effect of the thermal story and nonstoichiometry	
A. Chabli, E. Molva, J.P. Le Ludec, P. Bunod, C. Perret and F. Bertin	679
Influence of the shallow donors on the formation of gettering regions in Czochralski GaAs	
C. Frigeri and O. Breitenstein	685
Appearance of dislocations and precipitates in GaAs single crystals analyzed by γ -diffractometry and TEM-investigations	
H. Rüfer, W. Uelhoff, P. Schloßmacher and K. Urban	691
Non-uniform composition distribution in A^3B^5 single crystals derived from distribution of "quasi-forbidden" X-ray reflections integral intensity	
A.G. Efimov, A.V. Markov, M.G. Milvidsky and V.B. Osvensky	695
Photoluminescence topography studies in III/V semiconductors	
P.W. Epperlein	699
Microprecipitates and qualification of InP wafers	
P. Gall, J.-M. Lussert, J.-P. Fillard and E.V.K. Rao	705

[†] Invited paper.

Defect formation in sulphur doped InAs single crystals N.A. Anastasjeva, V.T. Bublic, V.V. Karataev, M.G. Milvidsky and T.G. Yugova	711
<i>Section III.2: Native defects and impurities in III-V compounds</i>	
Raman spectroscopy of impurities in GaAs [†] J. Wagner	715
Native defect interactions in GaAs [†] H.J. von Bardeleben and J.C. Bourgoin	725
Intrinsic acceptors and the structure of EL2 in semi-insulating gallium-arsenide [†] B.K. Meyer, K. Krambrock, D.M. Hofmann and J.-M. Spaeth	735
Generation and annihilation of EL2 in GaAs [†] M. Suezawa	745
Optical spectroscopy of EL2 centers in GaAs I.A. Buyanova, S.S. Ostapenko and M.K. Sheinkman	753
Relaxation processes of optically excited EL2 in GaAs Y. Mori, Y. Yoshimura, H. Kamoda, A. Honda, K. Onozawa, H. Ohkura and Y. Chiba	759
Optical properties of the metastable EL2* state J. Jiménez, A. Alvarez, J. Bonnafé and M.A. Gonzáles	765
A mechanism for EL2-related activation of Si implanted into semi-insulating GaAs F. Orito, Y. Yamada, K. Katano, F. Yajima and T. Okano	771
Defects in III-V compounds in thermal equilibrium up to 800 K P. Mascher, S. Dannefaer, D. Kerr and W. Puff	777
<i>Section III.3: Defect control through thermal treatments and defect passivation</i>	
Thermally induced changes in dislocations and associated defects in bulk GaAs [†] D.J. Stirland	783
The annealing behaviour of GaAs through defects and electrical device performances characterization [†] S. Martin	795
Control of inhomogeneities in semi-insulating GaAs by rapid cooling and annealing S. Clark, M.R. Brozel, D.J. Stirland, D.T.J. Hurle and I. Grant	807
Influence of heat-treatment on the distribution of non-radiative recombination centers in GaAs T. Sekiguchi and K. Sumino	813
Electronic paramagnetic resonance of As overpressure-induced defects in GaAs E. Christoffel, A. Goltzené, C. Schwab, K. Chino and K. Satoh	819

[†] Invited paper.

Annealing behavior of point defects in semi-insulating GaAs as observed by NMR spin echo method M. Suemitsu and N. Miyamoto	825
Point defects generated in thermally annealed LEC SI GaAs single crystals J. Ogata, N. Ohkubo and S. Matsumoto	829
Suppression of defects which limit carrier lifetime in bulk gallium arsenide D. Wong, H.K. Kim, Z.Q. Fang, T.E. Schlesinger and A.G. Milnes	835
Annealing effect on the electrical properties of Fe doped semi-insulating InP H. Shimakura, K. Kainosho, T. Inoue, H. Yamamoto and O. Oda	841
Defect passivation of GaAs surface by phosphidization T. Sugino, T. Yamada and J. Shirafuji	849
Hydrogen interaction with defects and impurities in III-V materials E.M. Omeljanovsky, A.V. Pakhomov and A.Y. Polyakov	855
Hydrogen passivation of impurities in gallium phosphide Y. Mochizuki, M. Mizuta, N. Takadoh and K. Asakawa	861
Hydrogen passivation of defects and impurities in InP E.M. Omeljanovsky, A.V. Pakhomov, A.Y. Polyakov, O.M. Borodina and G.V. Shepekina	867
Defect passivation in InP by phosphorus-added hydrogen plasma T. Sugino, A. Boonyasirikool and J. Shirafuji	873
Effect of hydrogenation on the photoluminescence properties of p-type InP V. Swaminathan, J. Lopata, S.E.G. Slusky, W.C. Dautremont-Smith and S.J. Pearton	879
<i>Section III.4: Defects induced by ion-implantation and particle-irradiation</i>	
Luminescent diagnostics of defects in ion-implanted III-V and II-VI semiconductors [†] A.A. Gippius, V.V. Ushakov and V.M. Konnov	885
Defects in H implanted GaAs studied by low-energy positron and ion-beam techniques K. Saarinen, P. Hautojärvi, J. Mäkinen, A. Vehanen, J. Keinonen, E. Rauhala, J. Koponen and C. Corbel	891
Photoacoustic study of the annealing behavior of ion-implanted GaAs T. Matsumori, M. Kawase, H. Maeto and T. Izumi	897
Lattice site prevalence of ion implanted Li in GaAs S. Winter, S. Blässer, H. Hofsäss, S. Jahn, G. Lindner, U. Wahl and E. Recknagel	903
Infrared absorption and reflection of N ⁺ -ion implanted InP H. Yoshinaga, F. Uehara and T. Matsumori	907
Study of plasma-process induced defects through threshold voltage change of GaAs MESFETs H. Furukawa, M. Nishiuma, M. Hagio, M. Kazumura and G. Kano	911

[†] Invited paper.